

**AMENDMENT TO THE CLAIMS:**

A listing of all the claims pending is presented below. Please amend the claims as indicated.

1. (Original) A method of operating a sense amplifier to read data stored in a memory cell, the method comprising steps of:

pre-charging a lit-line of the memory cell to a predetermined reference voltage substantially equal to a trip point of the sense amplifier using a pre-charging circuit;  
developing a voltage signal representing data stored in the memory cell;  
reconfiguring the pre-charge circuit as a regeneration circuit; and  
amplifying the voltage signal using the regeneration circuit.

2. (Original) A method according to claim 1, further including the step of pre-charging a node of a cascode device coupled to the bit-line of the memory cell.

3. (Cancelled)

4. (Cancelled)

5. (Re-presented – formerly dependent claim #5) A sense amplifier to read a multi-state memory cell having a field effect transistor (FET) with a source, a drain and a bit-line, the sense amplifier comprising:

a device coupled to the drain of the FET of the memory cell, the device adapted to increase the resolution of the sense amplifier during a read mode and to isolate the sense amplifier from a high voltage applied to the memory cell during a write mode; and

a pre-charge circuit coupled to a device, the pre-charge circuit configured to pre-charge the bit-line of the memory cell through the cascode device during a pre-charge mode to reduce time required to read the multi-state memory cell,

wherein the pre-charge circuit comprises a unity gain buffer having an input to which a predetermined reference voltage is applied, and an output coupled to provide a bias current ( $I_{BIAS}$ ) to the cascode device to pre-charge the bit-line by charging a node of the cascode device to the predetermined reference voltage.

6. (Original) A sense amplifier according to claim 5, wherein the pre-charge circuit further comprises a transistor switch to couple the unity gain buffer to the cascode

device during the pre-charge mode and to de-couple the unity gain buffer from the cascode device during a develop mode.

7. (Original) A sense amplifier according to claim 6, further comprising a reference current circuit to provide a reference current ( $I_{REF}$ ), wherein the develop mode a difference between  $I_{REF}$  and a current through the memory cell ( $I_{CELL}$ ) causes a change from the predetermined reference voltage to which the node of the cascode device is charged to develop a voltage signal representing data stored in the memory cell.

8. (Original) A sense amplifier according to claim 7, wherein the pre-charge circuit is re-configurable as a regeneration circuit during a regeneration mode to amplify the voltage signal developed during the develop mode.

9. (Cancelled)

10. (Original) In a memory having at least one multi-state memory cell capable of storing data therein and a sense amplifier capable of reading data stored in the memory cell, the sense amplifier having a cascode device coupled to the memory cell and a pre-charge circuit for pre-charging a bit-line of the memory cell through the cascode device, a method of operating the memory to read data stored in the multi-state memory cell, the method comprising the steps of:

- coupling the pre-charge circuit to the cascode device;
- pre-charging the bit-line of the memory cell through the cascode device to a predetermined reference voltage;
- de-coupling the pre-charge circuit from the cascode device;
- developing a voltage signal representing data stored in the memory cell;
- reconfiguring the pre-charge circuit as a regeneration circuit; and
- amplifying the voltage signal using the regeneration circuit.

11. (Original) A method according to claim 10, wherein the pre-charge circuit comprises a unity gain buffer having an output switchably coupled to the cascode device, and wherein the step of coupling the pre-charge circuit to the cascode device includes applying a control signal to couple the output to the cascode device.

12. (Original) A method according to claim 11, wherein the step of pre-charging the cascode device to a predetermined reference voltage includes:

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applying the predetermined reference voltage to an input to the unity gain buffer; and

applying a bias current ( $I_{BIAS}$ ) from the unity gain buffer to the cascode device to pre-charge the bit-line of the memory cell by charging the node of the cascode device to the predetermined reference voltage.

13. (Original) A method according to claim 12, wherein the sense amplifier further comprises a reference current circuit to provide a reference current ( $I_{REF}$ ) to the cascode device, and wherein the step of pre-charging the cascode device to a predetermined reference voltage includes applying  $I_{REF}$  and  $I_{BIAS}$  simultaneously to the cascode device to pre-charge the bit line through the cascode device to the predetermined reference voltage.

14. (Original) A method according to claim 13, wherein the step of developing a voltage signal includes enabling a difference between  $I_{REF}$  and a current through the memory cell ( $I_{CELL}$ ) to cause a change from the predetermined reference voltage to which the cascode device is charged.

15. (Original) A method according to claim 10, wherein the step of reconfiguring the pre-charge circuit as a regeneration circuit includes forming an amplifier having a positive feedback loop.

16. (Original) A method according to claim 15, wherein the pre-charge circuit comprises a unity gain buffer, and wherein forming an amplifier includes forming the amplifier using components comprising the unity gain amplifier.

17. (Original) A method according to claim 15, wherein the step of amplifying the voltage signal includes amplifying the voltage signal using the amplifier.

18. (Amended) A multi-state memory comprising:  
at least one multi-state memory cell capable of storing data therein;  
a sense amplifier capable of reading data stored in the memory cell, the sense amplifier including:

a cascode device coupled to the memory cell;

~~means for~~ a pre-charging circuit for pre-charging a bit-line of the at least one multi-state memory cell through the cascode device;

~~means for a developing circuit for~~ developing a voltage signal representing data stored in the memory cell using a reference current; and

~~means for an~~ amplifying circuit for amplifying the voltage signal.

19. (Currently amended) A multi-state memory comprising:

at least one multi-state memory cell capable of storing data therein;

a sense amplifier capable of reading data stored in the memory cell, the sense amplifier including:

a cascode device coupled to the memory cell;

a pre-charging circuit for pre-charging a bit-line of the at least one multi-state memory cell through the cascode device;

a developing circuit for developing a voltage signal representing data stored in the memory cell using a reference current; and

an amplifying circuit for amplifying the voltage signal,

wherein the pre-charging circuit comprises a unity gain buffer having an input to which a predetermined reference voltage is applied, and an output coupled to provide a bias current ( $I_{BIAS}$ ) to the cascode device to pre-charge the bit-line by charging the node of the cascode device to the predetermined reference voltage.

20. (Currently amended) A multi-state memory according to claim 19, wherein the

~~means for developing a voltage signal~~ developing circuit comprises:

means for decoupling the output of the pre-charge circuit from the cascode device; and a reference current circuit to provide a reference current ( $I_{REF}$ ) to the cascode device;

wherein a difference between  $I_{REF}$  and a current through the memory cell ( $I_{CELL}$ ) causes a change from the predetermined reference voltage to which the node of the cascode device is charged.

21. (Currently amended) A multi-state memory according to claim 19, wherein the

means for developing a voltage signal ~~developing circuit~~ comprises a regeneration circuit having an amplifier with a positive feedback loop.

22. (Original) A multi-state memory according to claim 21, wherein the pre-

charging circuit comprises components of the unity gain amplifier coupled together in a first

configuration, and wherein the regeneration circuit comprises components of the unity gain amplifier coupled together in a second configuration.